# onsemi

# **N-Channel Switch**

# J111, J112, J113, MMBFJ111, MMBFJ112, MMBFJ113

### Features

- This Device is Designed for Low Level Analog Switching, Sample and Hold Circuits and Chopper Stabilized Amplifiers
- Sourced from Process 51
- Source & Drain are Interchangeable
- These are Pb-Free Devices

# **ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit
V <sub>DG</sub>	Drain-Gate Voltage	35	V
V <sub>GS</sub>	Gate-Source Voltage	-35	V
I <sub>GF</sub>	Forward Gate Current	50	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	–55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

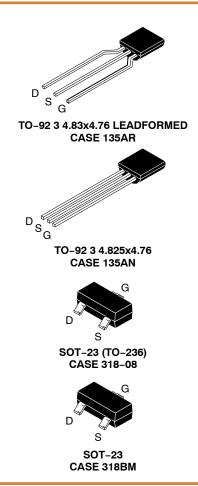
- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

#### THERMAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

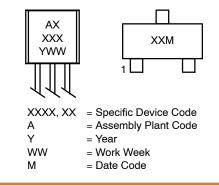
		Ma	ax	
Symbol	Parameter	J111 / J112 / J113 (Note 3)	MMBFJ111 / MMBFJ112 / MMBFJ113 (Note 4)	Unit
PD	Total Device Dissipation	625	350	mW
	Derate Above 25°C	5.0	2.8	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case	125	-	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient	200	357	°C/W

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

 Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm<sup>2</sup>.



#### MARKING DIAGRAMS



### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 6 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Test Condit	Test Condition		Max	Unit
OFF CHARA	ACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	$I_G = -1.0 \ \mu A, \ V_{DS} = 0$		-35	-	V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -15 \text{ V}, V_{DS} = 0$		-	-1.0	nA
V <sub>GS</sub> (off)	Gate-Source Cut-Off Voltage	$V_{DS}$ = 5 V, $I_D$ = 1.0 $\mu$ A	111	-3.0	-10.0	V
			112	-1.0	-5.0	
			113	-0.5	-3.0	1
I <sub>D</sub> (off)	Drain Cutoff Leakage Current	$V_{DS} = 5.0 \text{ V}, V_{GS} = -10 \text{ V}$	V	-	1.0	nA
	Drain Cutoff Leakage Current	$V_{DS} = 5.0 \text{ V}, V_{GS} = -10 \text{ V}$	V	-	1.0	•

#### **ON CHARACTERISTICS**

I <sub>DSS</sub>	Zero-Gate Voltage Drain Current (Note 5)	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0$	111	20	-	mA
			112	5.0	-	
			113	2.0	-	
r <sub>DS</sub> (on)	Drain-Source On Resistance	$V_{DS} \leq 0.1 \text{ V},  V_{GS} = 0$	111	-	30	Ω
			112	-	50	
			113	_	100	]

#### SMALL SIGNAL CHARACTERISTICS

C <sub>dg</sub> (on) C <sub>sg</sub> (on)	Drain-Gate &Source-Gate On Capacitance	$V_{DS}$ = 0, $V_{GS}$ = 0, f = 1.0 MHz	-	28	pF
C <sub>dg</sub> (off)	Drain-Gate Off Capacitance	$V_{DS}$ = 0, $V_{GS}$ = –10 V, f = 1.0 MHz	-	5.0	pF
C <sub>sg</sub> (off)	Source-Gate Off Capacitance	$V_{DS}$ = 0, $V_{GS}$ = -10 V, f = 1.0 MHz	-	5.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulse test: pulse width  $\leq$ 300  $\mu$ s, duty cycle  $\leq$ 2%.

## **TYPICAL PERFORMANCE CHARACTERISTICS**

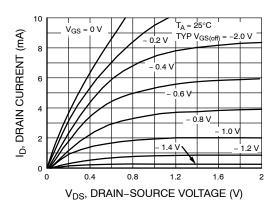


Figure 1. Common Drain–Source

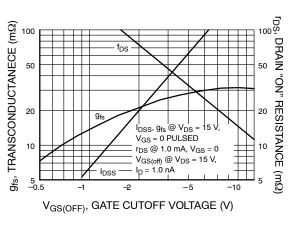


Figure 2. Parameter Interactions

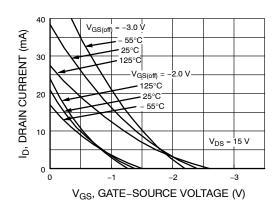


Figure 3. Transfer Characteristics

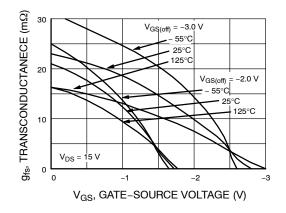


Figure 5. Transfer Characteristics

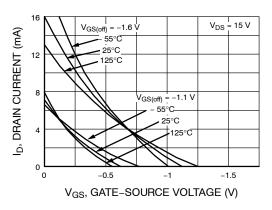


Figure 4. Transfer Characteristics

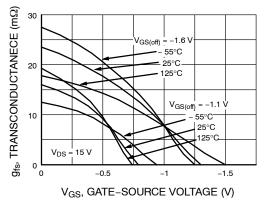


Figure 6. Transfer Characteristics

# TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

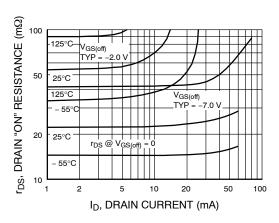


Figure 7. On Resistance vs. Drain Current

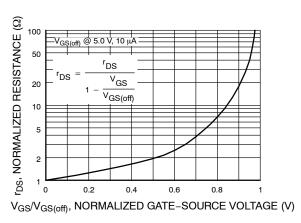


Figure 8. Normalized Drain Resistance vs. Bias Voltage

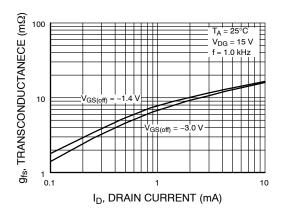


Figure 9. Transconductance vs. Drain Current

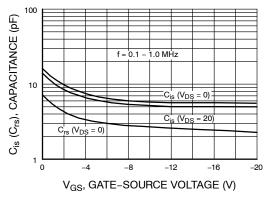


Figure 11. Capacitance vs. Voltage

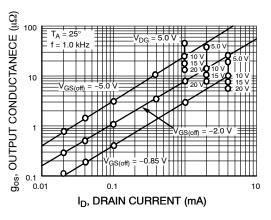


Figure 10. Output Conductance vs. Drain Current

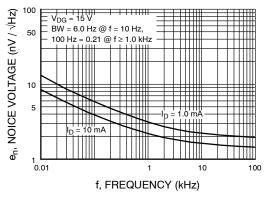


Figure 12. Noise Voltage vs. Frequency

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

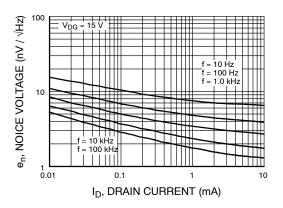


Figure 13. Noise Voltage vs. Current

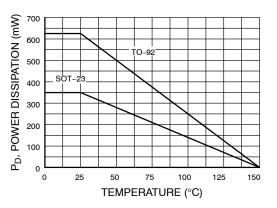


Figure 14. Power Dissipation vs. Ambient Temperature

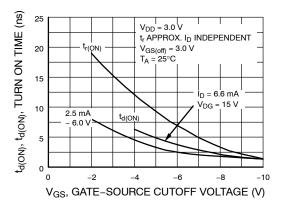


Figure 15. Switching Turn-On Time vs. Gate-Source Voltage

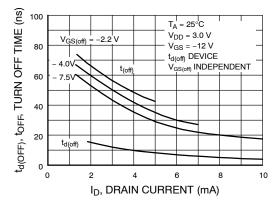


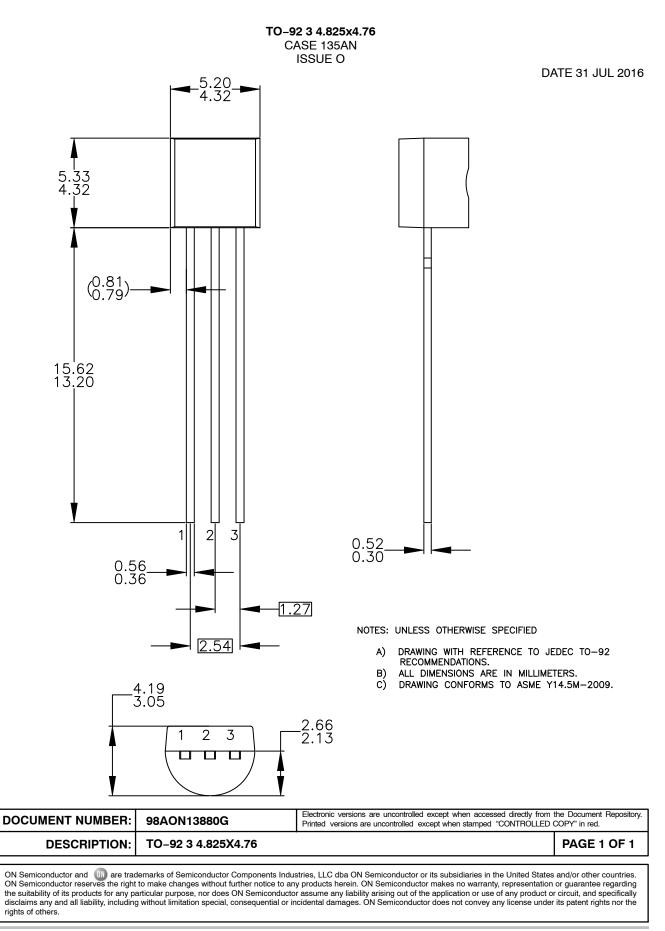
Figure 16. Switching Turn-Off Time vs. Drain Current

## **ORDERING INFORMATION**

Part Number	Top Mark	Package	Shipping <sup>†</sup>
J111	AJ 111 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J111-D26Z	AJ 111 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J111-D74Z	AJ 111 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
J112	AJ 112 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J112-D26Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112–D27Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Tape & Reel
J112–D74Z	AJ 112 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
J113	AJ 113 YWW	TO-92 3L (Pb-Free)	10000 Units / Bulk
J113-D74Z	AJ 113 YWW	TO-92 3L (Pb-Free)	2000 / Ammo
MMBFJ111	6P	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ112	6R	SOT-23 3L (Pb-Free)	3000 / Tape & Reel
MMBFJ113	6S	SOT-23 3L (Pb-Free)	3000 / Tape & Reel

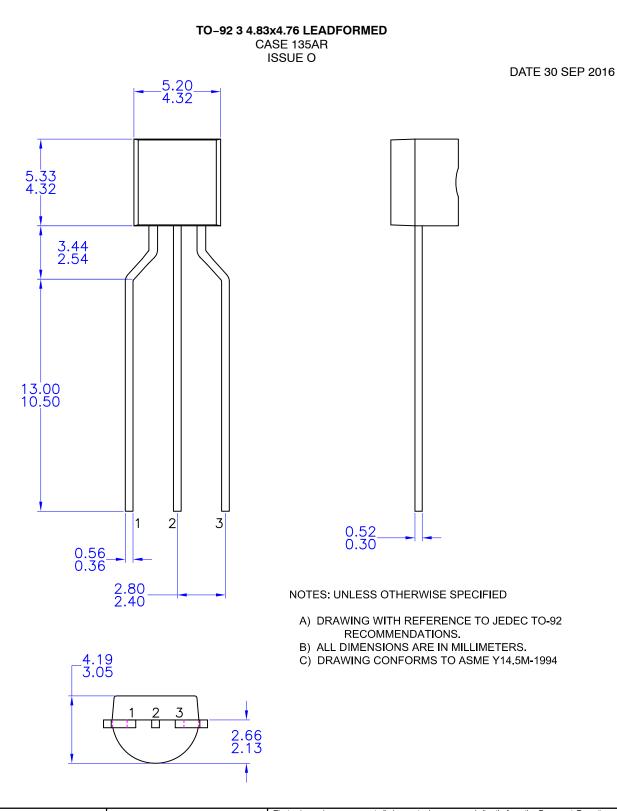
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

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TOP VIEW

SIDE VIEW

Нe

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SCALE 4:1

A\_\_\_\_ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

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DETAIL A

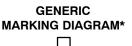
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



DETAIL A



- XXX = Specific Device Code
- M = Date Code
- = Pb–Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

# **STYLES ON PAGE 2**

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# MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

# onsemi

#### SOT-23 (TO-236) CASE 318 ISSUE AT

#### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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